

REMARKS

In response to the Restriction Requirement set forth in this Office Action, Applicant affirms election of Group I, Claims 1-10, 19, 20. This election is made with traverse.

Claims 1-10, 19 20 stand rejected under 35 USC 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claims 1, 2, 4-8, and 19 stand rejected under 35 USC 102(b) as anticipated by US Patent 5,462,700 to Beeson, et al.

Claims 3, 9, 10, and 20 stand rejected under 35 USC 103(a) as being unpatentable over Beeson as applied to claim 1 in view of US Patent 5,782,460 to Kretzschmar, et al.

Claim 1 further stands rejected under 35 USC 103(a) as being unpatentable over US patent 5,545,367 to Bae, et al in view of Beeson.

Claims 19 and 20 are hereby canceled, and claim 1 is hereby amended to include the feature that the optical structure is defined by moving a beam from the laser in a controlled pattern. Support for this amendment is found at page 5, line 32 and page 6, lines 26 – 28. Reconsideration and allowance of the claims as amended is requested for the following reasons.

Applicants invention is directed to a method for generating optical structures in a photoresist that includes forming a pool of photoresist on a first side of a transparent substrate; exposing the photoresist to create a predetermined three-dimensional pattern of optical structures using a laser positioned on second side of the transparent substrate opposite the first side by moving the focal point of a beam from the laser in a controlled pattern to define the optical structure; developing the exposed predetermined pattern leaving a developed portion and an undeveloped portion; and removing either the developed portion or the undeveloped portion of the photoresist.

Beeson et al. disclose a process for making an array of tapered waveguides by exposing a photopolymerizable mixture on a transparent substrate through a mask located on the back-side of the substrate. One limitation of this approach is that light is diffracted by the edges of the mask to form an indistinct pattern on the photo resist as the substrate thickness increases. The present

invention avoids this problem by focusing a laser beam through the substrate onto the photoresist and moving the focal point of the laser beam to define the pattern. Claim 1 is hereby amended to include this feature of the invention. None of the other references cited by the Examiner teach, show or suggest moving the focal point of a laser beam directed through a substrate to define a pattern in the photoresist. It is believed therefore that amended claim 1 is patentable over Beeson et al. alone or in combination with any of the other cited references. The remainder of the Claims pending in the application depend from claim 1 and are believed to be patentable for at least the same reasons.

It is believed that the claims in the application are allowable over the prior art and such allowance is respectfully requested.

Respectfully submitted,



Attorney for Applicant(s)
Registration No. 27,428

Thomas H. Close/gms
Rochester, NY 14650
Telephone: 585-722-2396
Facsimile: 585-477-4646